MOSFETs Silicon Carbide N-Channel MOS

TW070J120B

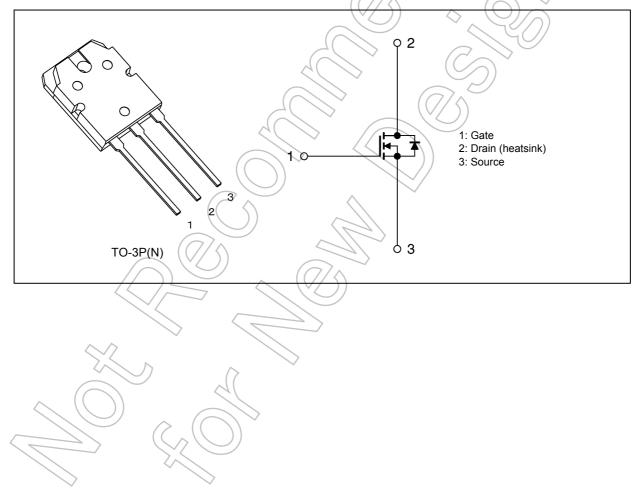
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 2nd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: $V_{DSF} = -1.35 V$ (typ.)
- (3) High voltage: $V_{DSS} = 1200 V$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 70 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: $V_{th} = 4.2$ to 5.8 V ($V_{DS} = 10$ V, $I_D = 20$ mA)
- (6) Enhancement mode.

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25$ °C unless otherwise specified)

Charao	cteristics		Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	1200	V
Gate-source voltage			V _{GSS}	+25/-10	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	36.0	A
Drain current (DC)	(T _c = 100 °C)	(Note 1)	Ι _D	25.5	
Drain current (pulsed)		(Note 1)	I _{DP}	72	
Power dissipation	(T _c = 25 °C)		PD	272	W
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	
Mounting torque			TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics		$(\bigcirc / \land$	Symbol	Max	Unit
Channel-to-case thermal resistance	$\langle \rangle$		R _{th(ch-c)}	0.55	°C/W
Channel-to-ambient thermal resistance			R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V_{GS} = +25/-10 V, V_{DS} = 0 V	_	_	±0.5	μA
Drain cut-off current		I _{DSS}	V _{DS} = 1200 V, V _{GS} = 0 V	Ľ	0.2	10	
			T _a = 175 °C, V _{DS} = 1200 V, V _{GS} = 0 V	$\langle \rangle$	3.0	—	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 1 mA, V _{GS} = 0 V	1200	ジ ー		V
Gate threshold voltage	(Note 2)	V _{th}	V _{DS} = 10 V, I _D = 20 mA	4.2	_	5.8	
Drain-source on-resistance		R _{DS(ON)}	V _{GS} = 20 V, I _D = 18 A		70	90	mΩ
			T _a = 150 °C, V _{GS} = 20 V, I _D = 18 A	$\geq -$	87	_	

Note 2: Please be sure to I_{GSS} (V_{GS} = 25 V) test before the V_{th} test.

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C _{iss}	$V_{DS} = 800 V, V_{GS} = 0 V,$	\sim	1680	_	pF
Reverse transfer capacitance	C _{rss}	f = 100 kHz		8	-	
Output capacitance	C _{oss}		~_)	109		
C _{oss} stored energy	E _{oss}			42	_	μJ
Gate resistance	r _g	V _{DS} = OPEN, f = 100 kHz	U –	3.5	_	Ω
Turn-on delay time	t _{d(on)}	See Fig. 6.5.1	_	17	_	ns
Switching time (rise time)	tr	See Fig. 6.5.2	_	7	_	
Turn-off delay time	t _{d(off)}		_	40	_	
Switching time (fall time)	tf		_	35	_	
Turn-on switching loss	Eon		_	0.380	_	mJ
Turn-off switching loss	Eoff			0.035	_	

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

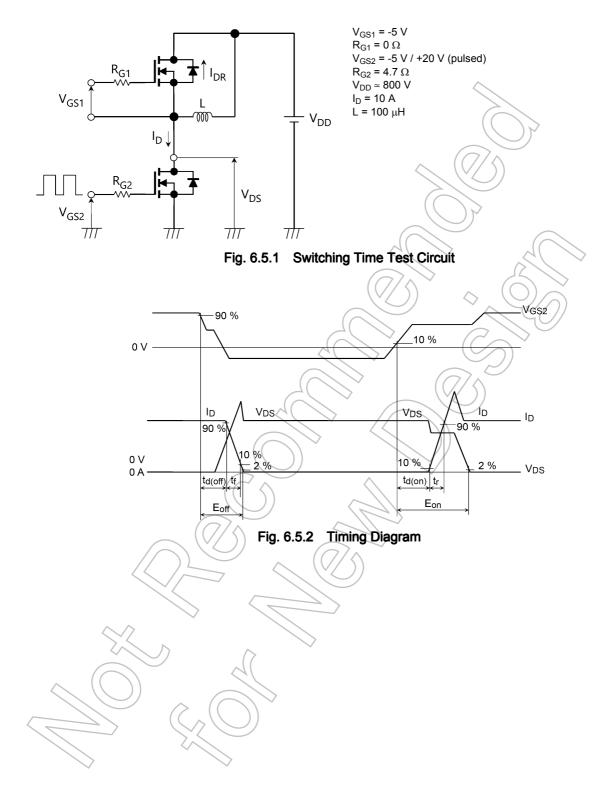
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		V _{DD} ≈ 800 V, V _{GS} = 20 V, I _D = 18 A	—	67	—	nC
Gate-source charge 1	Q _{gs1}		_	13	_	
Gate-drain charge	Q _{gd}	\checkmark	_	25	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

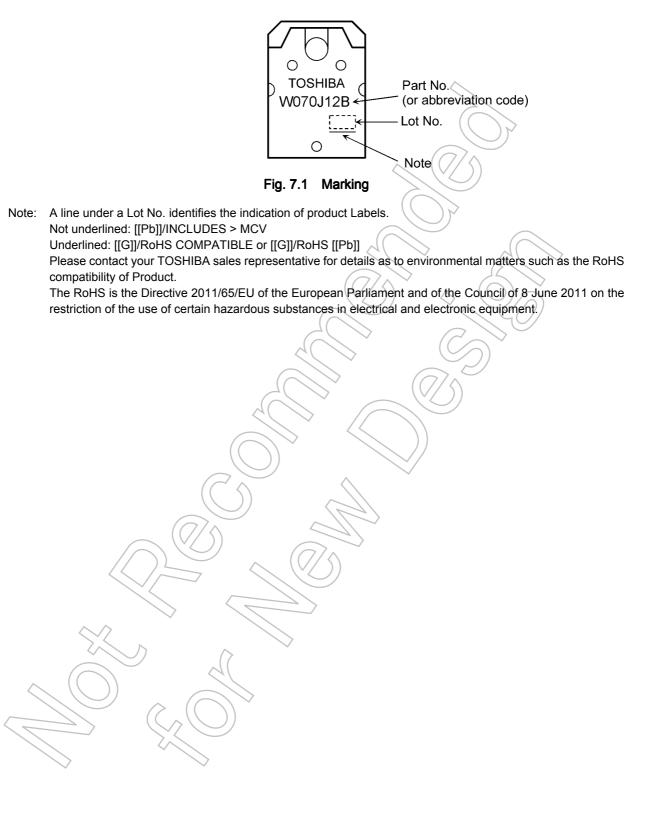
Characteristics	$\left(2 \right) \left(2 \right)$	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward current (DC)	(Note 3)	I⊧	T _c = 25 °C	_	_	36	А
		>	T _c = 100 °C		_	29.6	
Diode forward current	(Note 3)	I _{FP}	T _c = 25 °C	—	_	72	
(pulsed)		T _c = 100 °C	_	—	32		
Diode forward voltage		V _{DSF}	I _{DR} = 10 A, V _{GS} = -5 V		-1.35	-1.80	V
			T _a = 150 °C, I _{DR} = 10 A, V _{GS} = -5 V	—	-1.70	_	
Reverse recovery time		t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V,		22	—	ns
Reverse recovery charge		Q _{rr}	V _{DD} = 800 V, -dI _{DR} /dt = 1000 A/μs	_	170	_	nC
Peak reverse recovery current		I _{rr}		—	15	—	A

Note 3: Ensure that the channel temperature does not exceed 175 °C.

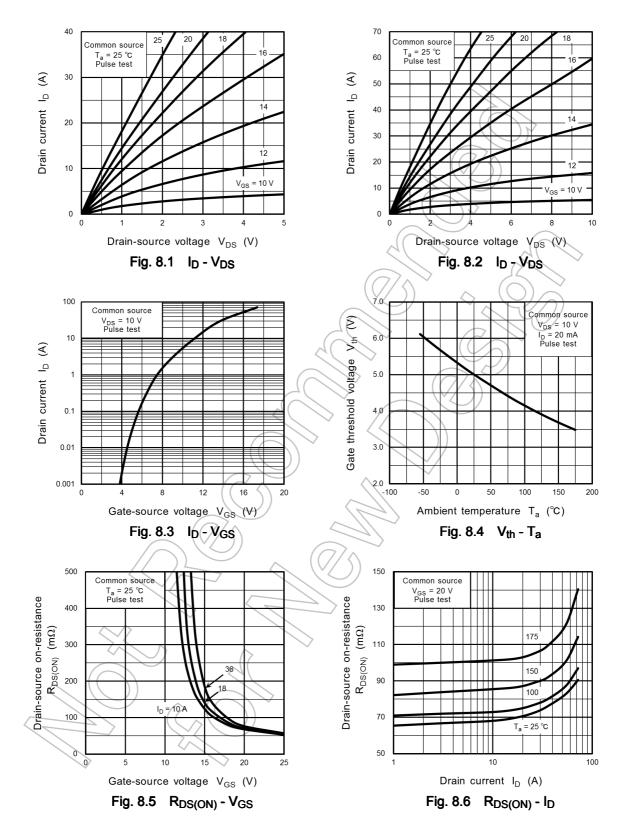
6.5. Test Circuit and Timing Diagram

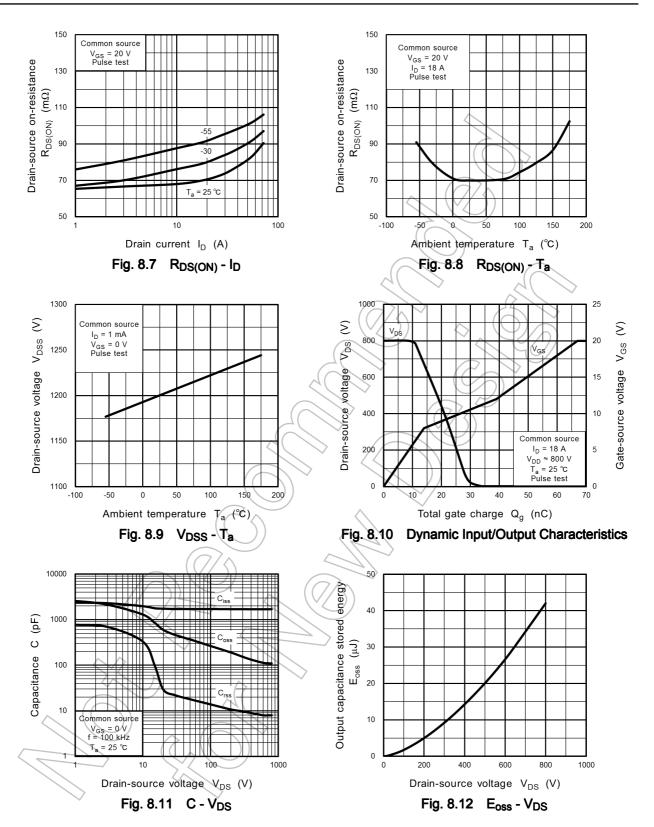


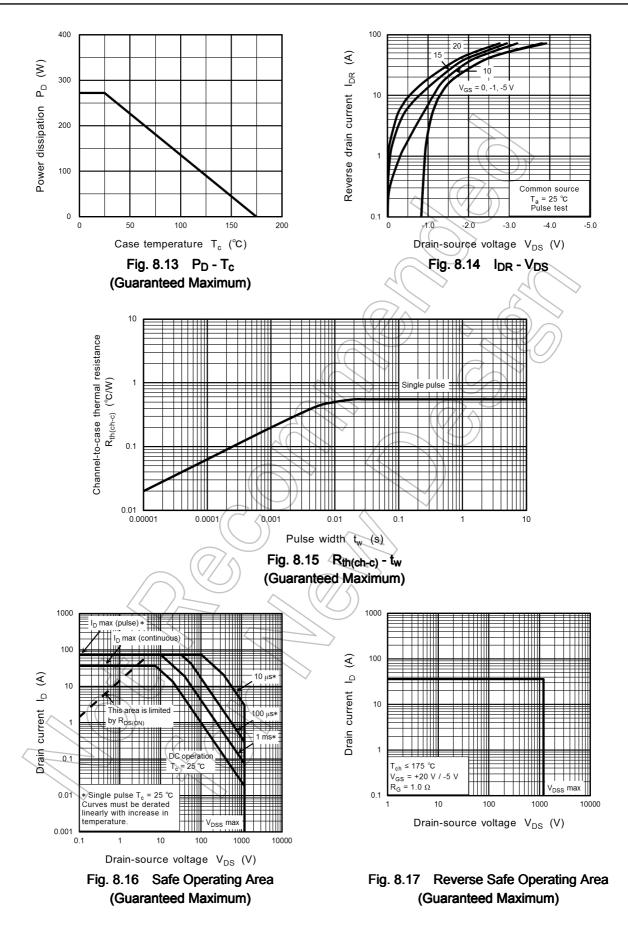
7. Marking (Note)



8. Characteristics Curves (Note)



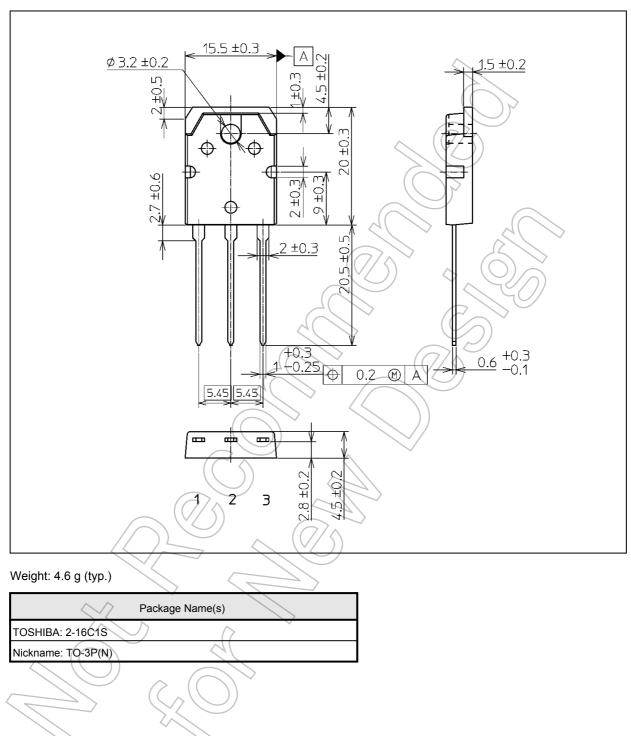




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



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